

AMENDMENTS TO THE CLAIMS:

Please amend the claims as follows:

1-10. (Canceled)

11. (Currently amended) An epitaxial growth method comprising:

growing an epitaxial layer on a layered substrate,

wherein the layered substrate comprises sapphire on silicon and the epitaxial layer

comprises group III nitrides, and

the epitaxial layer is grown on the opposite side of the sapphire from that of the silicon layer after formation of the silicon layer.

12-23. (Canceled)

24. (Previously presented) The epitaxial growth method of claim 11 further comprising the step of removing the layered substrate after growing the epitaxial layer.

25. (Previously presented) The epitaxial growth method of claim 24 wherein the step of removing comprises mechanical polishing.

26. (Previously presented) The epitaxial growth method of claim 11 wherein a process of forming said layered substrate includes a heating step, wherein said layered substrate exhibits [[the]] a bowing after being cooled down from said heating step.

27. (Canceled)

28. (Previously presented) The epitaxial growth method of claim 11, wherein the thickness of the silicon is less than 6 microns, the thickness of the epitaxial layer is less than 3 microns and the wafer bowing is less than 0.5 m^{-1} .

29. (Previously presented) The epitaxial growth method of claim 11, wherein the thickness of the silicon is from 2 to 10 microns, the thickness of the epitaxial layer is from 3 to 10 microns and the wafer bowing is less than 0.5 m^{-1} .

30. (Previously presented) The epitaxial growth method of claim 11, wherein the thickness of the silicon is from 20 to 30 microns, the thickness of the epitaxial layer is from 40 to 60 microns and the wafer bowing is less than 0.5 m^{-1} .

31. (Currently amended) An epitaxial growth method comprising the step of:
growing an epitaxial layer on a layered substrate, wherein the layered substrate ~~comprising~~ comprises sapphire on silicon ~~exhibits~~ exhibiting bowing in a convex manner and the epitaxial layer comprises group III nitrides,

wherein the epitaxial layer is grown on the opposite side of the sapphire from that of the silicon layer after formation of the silicon layer, and

flattening the epitaxial layer having a III-V nitrides alloy and the layered substrate by growing the epitaxial layer on the layered substrate,

wherein the formation of the epitaxial layer flattens the wafer.

32. (Previously presented) The epitaxial growth method of claim 31, wherein
an AlN buffer layer is grown on the layered substrate prior to growing the epitaxial layer thereon, and

the AlN buffer layer is grown at a temperature lower than that of the epitaxial layer.

33. (New) The epitaxial growth method of claim 11, wherein a surface of the epitaxial layer of the group III nitrides is not degraded by a reactant species for the formation of the silicon layer on the opposite side of the sapphire.

34. (New) The epitaxial growth method of claim 33, wherein a gas source containing nitrogen is used for the formation of the epitaxial layer of the group III nitrides.